

FORM PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE							ATTORNEY DOCKET NO 005552 USA/AMT		SERIAL NO N/A
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)		APPLICANT Yu, et al.							FILING DATE Herewith		GROUP UNKNOWN 2823

U.S. PATENT DOCUMENTS

Examiner Initial		DOCKET NUMBER							DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>Lee</i>	AA	4	7	3	2	7	6	1	03/22/88	Machida, et al.	204	192.32	<i>J1038 U.S. PTO 07/09/90 5053</i>
	AB	4	9	6	2	0	6	3	10/09/90	Maydan, et al.	437	228	
	AC	5	0	8	9	4	4	2	02/18/92	Olmer	204	192.3	
	AD	5	1	2	4	0	1	4	06/23/92	Foo, et al.	204	192.32	
	AE	5	2	0	4	2	8	8	04/20/93	Marks, et al.	437	228	
<i>Lee</i>	AF	5	2	4	4	8	4	1	09/14/93	Marks, et al.	437	228	<i>J1038 U.S. PTO 07/09/90 5053</i>
	AG												
	AH												
	AI												
	AJ												
	AK												

FOREIGN PATENT DOCUMENTS

		DOCKET NUMBER							DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION		
													YES	NO	
<i>Lee</i>	AL	0	5	2	0	5	1	9	12/30/92	EP				X	
	AM														
	AN														
	AO														
	AP														

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

<i>Lee</i>	AQ	Kuo, Y., "Etch Mechanism in the Low Refractive Index Silicon Nitride Plasma-enhanced Chemical Vapor Deposition Process." <u>Applied Physics Letters</u> , 63(2): 144-146 (1993)
<i>Lee</i>	AR	Machida, K., et al., "SiO ₂ Planarization Technology with biasing and Electron Cyclotron Resonance Plasma Deposition for Submicron Interconnections." <u>J. Vac. Sci. Technol. B</u> , 4(4): 818-821 (1986)
<i>Lee</i>	AS	Li, J., et al., "Modeling Studies of the Mechanisms in Biased ECR CVD"
<i>Lee</i>	AT	Lassig, S., et al., "Intermetal Dielectric Deposition by Electron Cyclotron Resonance Chemical Vapor Deposition (ECR CVD)." pp. 1-21

EXAMINER

Green May Lee

DATE CONSIDERED

7/17/2002

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.